

Features

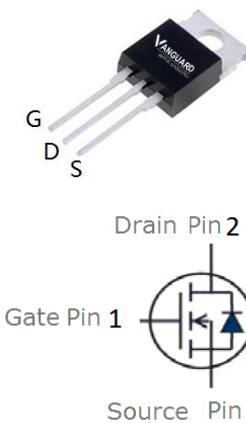
- N-Channel, 10V Logic Level Control
- Enhancement mode
- Very low on-resistance $R_{DS(on)}$ @ $V_{GS}=10$ V
- 100% Avalanche Tested
- Pb-free lead plating; RoHS compliant

V_{DS}	68	V
$R_{DS(on),TYP} @ V_{GS}=10$ V	6.1	$m\Omega$
I_D	105	A

TO-220AB



Part ID	Package Type	Marking	Tape and reel information
VS6880AT	TO-220AB	6880AT	50pcs/Tube



Maximum ratings, at $T_A=25$ °C, unless otherwise specified

Symbol	Parameter	Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage	68	V
V_{GS}	Gate-Source voltage	± 25	V
I_S	Diode continuous forward current	$T_C=25^\circ C$	A
I_D	Continuous drain current @ $V_{GS}=10$ V	$T_C=25^\circ C$	A
		$T_C=100^\circ C$	A
I_{DM}	Pulse drain current tested ①	$T_C=25^\circ C$	A
I_{DSM}	Continuous drain current @ $V_{GS}=10$ V	$T_A=25^\circ C$	A
		$T_A=70^\circ C$	A
EAS	Avalanche energy, single pulsed ②	225	mJ
P_D	Maximum power dissipation	$T_C=25^\circ C$	W
P_{DSM}	Maximum power dissipation ③	$T_A=25^\circ C$	W
T_{STG}, T_J	Storage and Junction Temperature Range	-55 to 175	°C

Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W



Electrical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ $T_j = 25^\circ\text{C}$ (unless otherwise stated)						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	68	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=65\text{V}, V_{\text{GS}}=0\text{V}$	--	--	1	μA
	Zero Gate Voltage Drain Current($T_j=125^\circ\text{C}$)	$V_{\text{DS}}=65\text{V}, V_{\text{GS}}=0\text{V}$	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	$V_{\text{GS}}=\pm 25\text{V}, V_{\text{DS}}=0\text{V}$	--	--	± 100	nA
$V_{\text{GS(TH)}}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2.5	2.9	3.9	V
$R_{\text{DS(ON)}}$	Drain-Source On-State Resistance ④	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=40\text{A}$	--	6.1	8	$\text{m}\Omega$
Dynamic Electrical Characteristics @ $T_j = 25^\circ\text{C}$ (unless otherwise stated)						
C_{iss}	Input Capacitance	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	4500	5855	7000	pF
C_{oss}	Output Capacitance		150	250	350	pF
C_{rss}	Reverse Transfer Capacitance		100	175	250	pF
R_g	Gate Resistance	f=1MHz	--	3	--	Ω
Q_g	Total Gate Charge	$V_{\text{DS}}=35\text{V}, I_{\text{D}}=40\text{A}, V_{\text{GS}}=10\text{V}$	--	86	--	nC
Q_{gs}	Gate-Source Charge		--	14	--	nC
Q_{gd}	Gate-Drain Charge		--	23	--	nC
Switching Characteristics						
$t_{\text{d(on)}}$	Turn-on Delay Time	$V_{\text{DD}}=35\text{V}, I_{\text{D}}=40\text{A}, R_{\text{G}}=3\Omega, V_{\text{GS}}=10\text{V}$	--	15	--	ns
t_r	Turn-on Rise Time		--	11.8	--	ns
$t_{\text{d(off)}}$	Turn-Off Delay Time		--	51	--	ns
t_f	Turn-Off Fall Time		--	18	--	ns
Source- Drain Diode Characteristics@ $T_j = 25^\circ\text{C}$ (unless otherwise stated)						
V_{SD}	Forward on voltage	$I_{\text{SD}}=40\text{A}, V_{\text{GS}}=0\text{V}$	--	0.9	1.2	V
t_{rr}	Reverse Recovery Time	$T_j=25^\circ\text{C}, I_{\text{SD}}=40\text{A}, V_{\text{GS}}=0\text{V}$ $dI/dt=100\text{A}/\mu\text{s}$	--	44	--	ns
Q_{rr}	Reverse Recovery Charge		--	33	--	nC

NOTE:

- ① Repetitive rating; pulse width limited by max junction temperature.
- ② Limited by $T_{j\text{max}}$, starting $T_j = 25^\circ\text{C}$, $L = 0.5\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 30\text{A}$, $V_{GS} = 10\text{V}$. Part not recommended for use above this value
- ③ The power dissipation P_{DSM} is based on R_{EJA} and the maximum allowed junction temperature of 150°C .
- ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.



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VS6880AT

68V/105A N-Channel Advanced Power MOSFET

Typical Characteristics

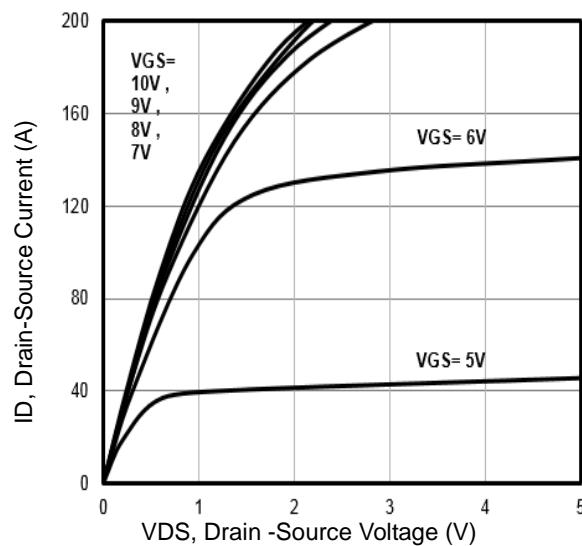


Fig1. Typical Output Characteristics

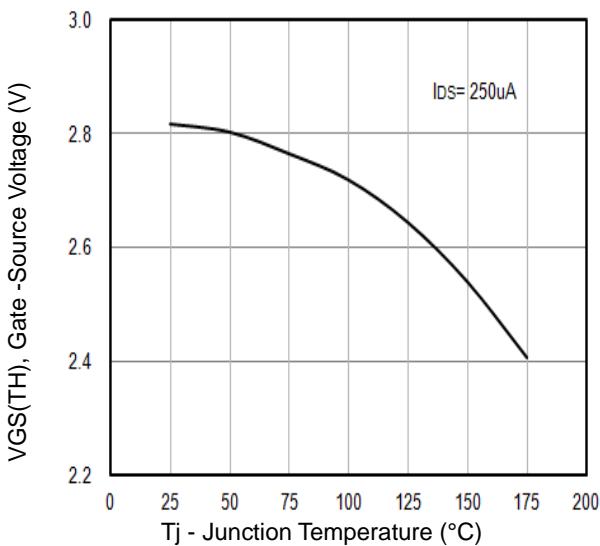


Fig2. $V_{GS(TH)}$ Gate -Source Voltage Vs. T_j

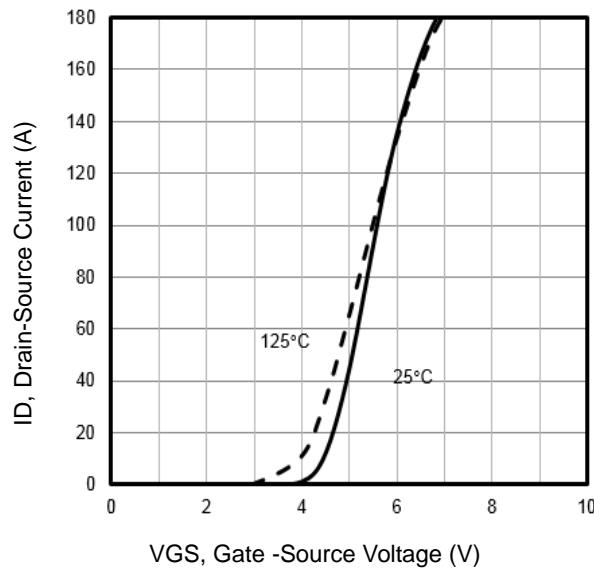


Fig3. Typical Transfer Characteristics

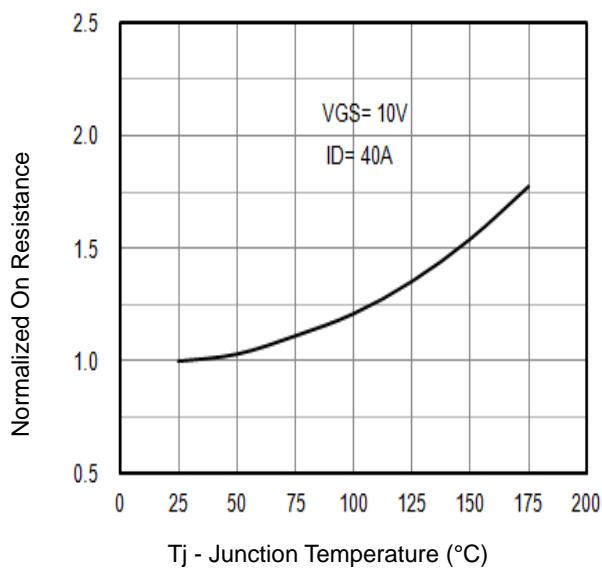


Fig4. Normalized On-Resistance Vs. Temperature

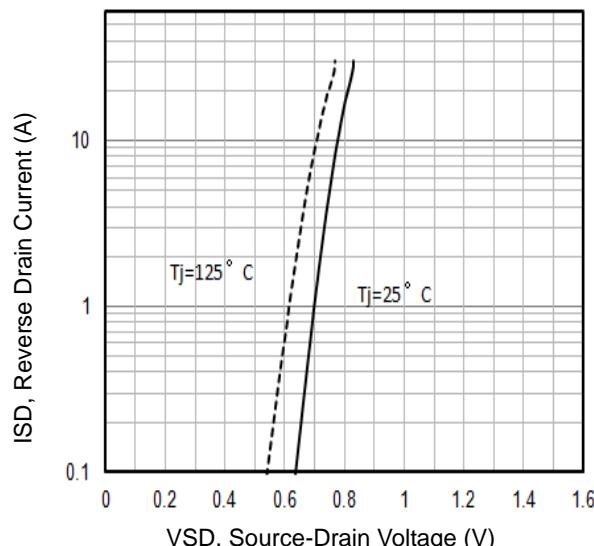


Fig5. Typical Source-Drain Diode Forward Voltage

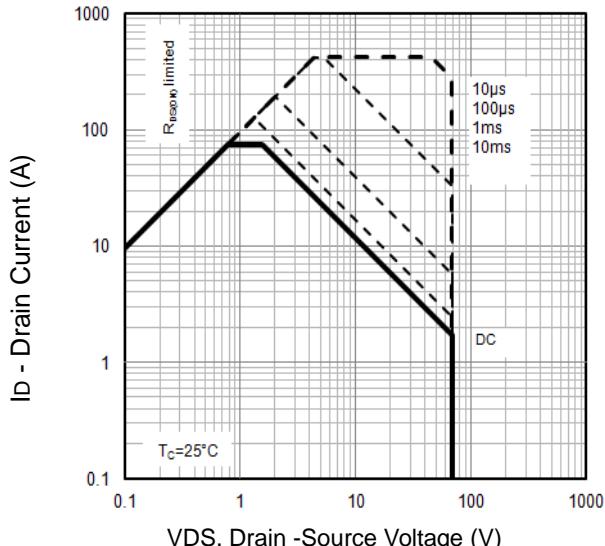


Fig6. Maximum Safe Operating Area

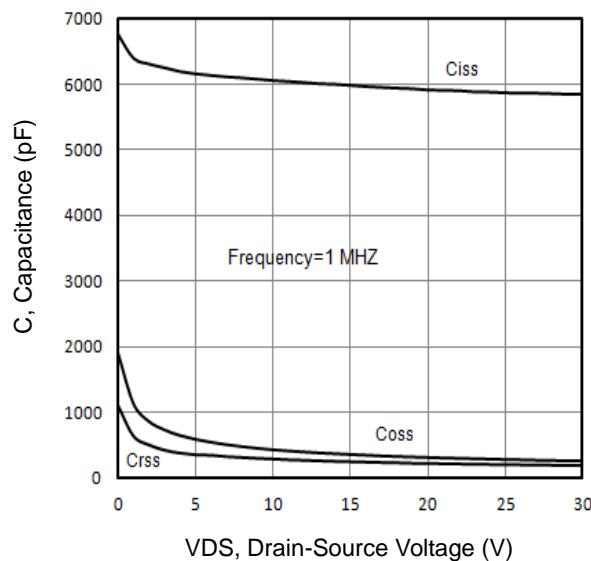


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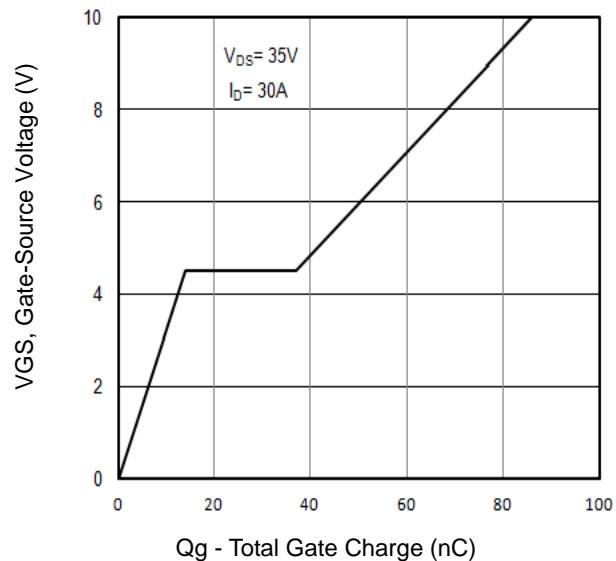
68V/105A N-Channel Advanced Power MOSFET

Typical Characteristics



VDS, Drain-Source Voltage (V)

Fig7. Typical Capacitance Vs. Drain-Source Voltage



Qg - Total Gate Charge (nC)

Fig8. Typical Gate Charge Vs. Gate-Source Voltage

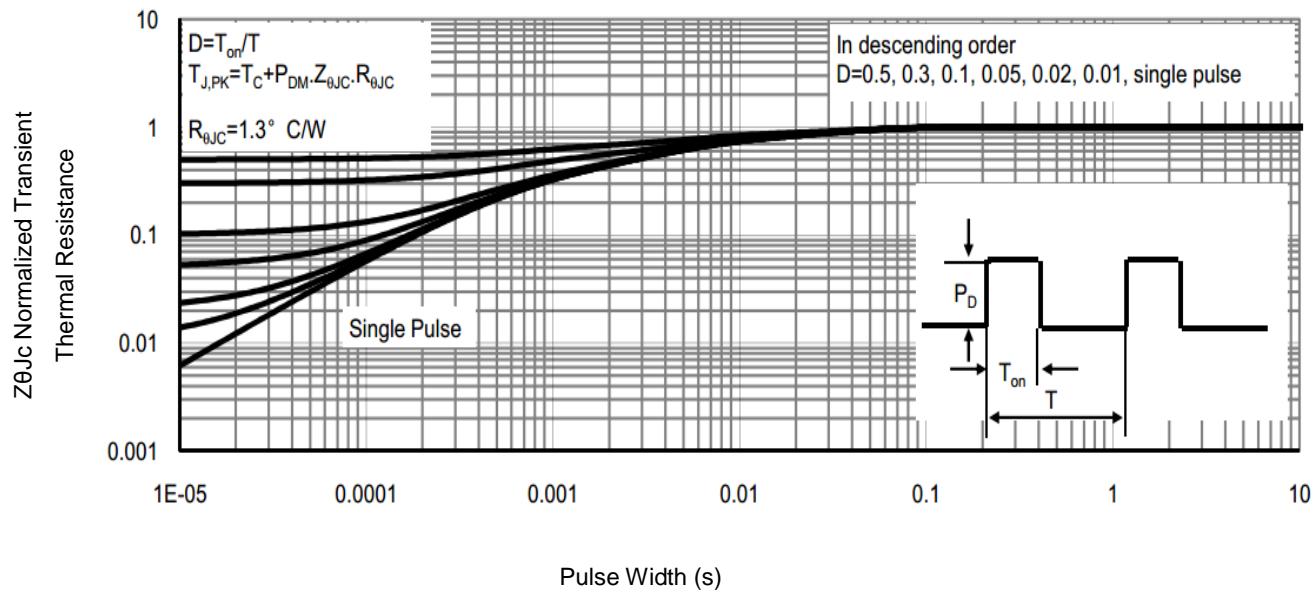


Fig9 . Normalized Maximum Transient Thermal Impedance

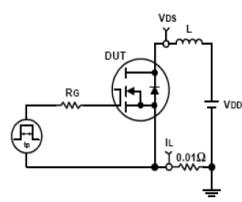


Fig10. Unclamped Inductive Test Circuit and waveforms

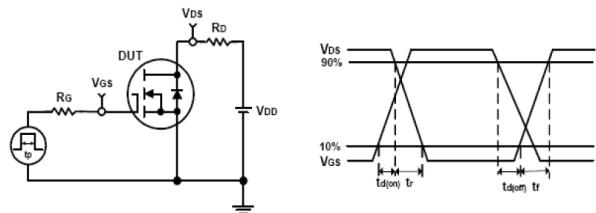


Fig11. Switching Time Test Circuit and waveforms

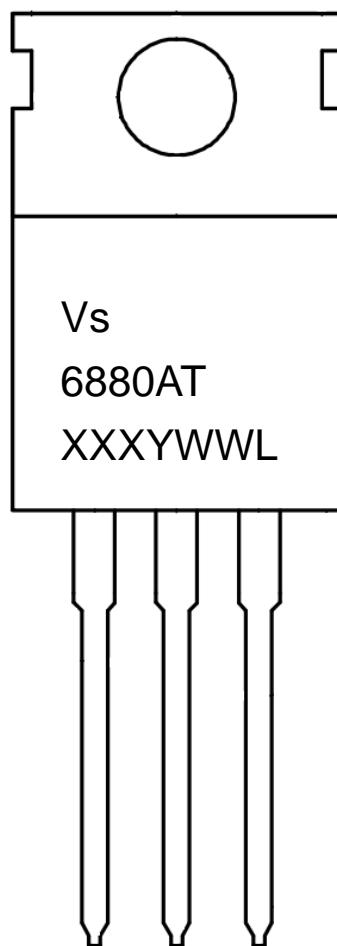


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VS6880AT

68V/105A N-Channel Advanced Power MOSFET

Marking Information



1st line: Vanguard Code (Vs)

2nd line: Part Number (6880AT)

3rd line: Date code (XXXYWWL)

XXX: Wafer Lot Number Code , code changed with Lot Number

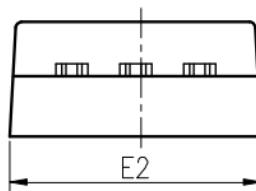
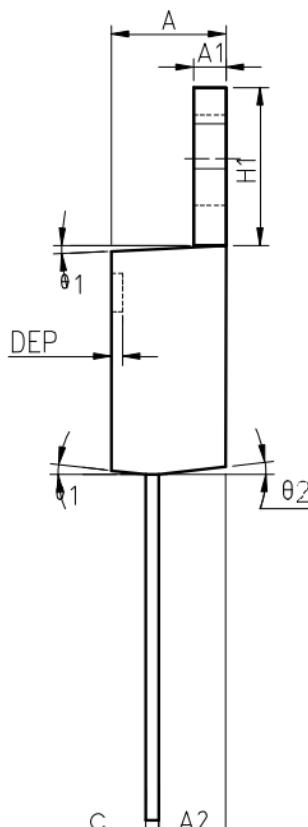
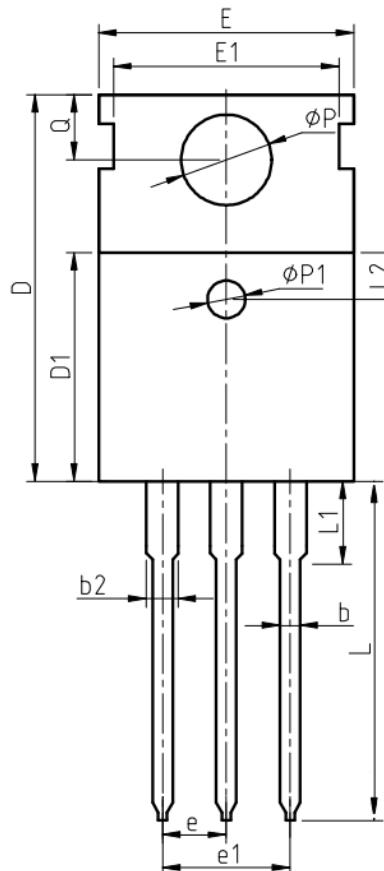
Y: Year Code, (e.g. E=2017, F=2018, G=2019, H=2020, etc)

WW: Week Code (01 to 53)

L: Class of $V_{GS(TH)}$



TO-220AB Package Outline Data



Symbol	Dimensions (unit: mm)		
	Min	Typ	Max
A	4.30	4.52	4.70
A1	1.15	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	1.00
b2	1.17	1.32	1.50
c	0.45	0.50	0.61
D	15.30	15.65	15.90
D1	9.00	9.20	9.40
DEP	0.05	0.10	0.25
E	9.66	9.90	10.28
E1	-	8.70	-
E2	9.80	10.00	10.20
φP1	1.40	1.50	1.60
e	2.54 BSC		
e1	5.08 BSC		
H1	6.40	6.50	6.80
L	12.70	-	14.27
L1	-	-	3.95
L2	2.40	2.50	2.60
φP	3.53	3.60	3.70
Q	2.70	2.80	2.90
θ1	5 °	7 °	9 °
θ2	1 °	3 °	5 °

Notes:

1. Refer to JEDEC TO-220 variation AB
2. Dimension "D" and "E" do NOT include mold flash. Mold flash shall not exceed 0.127mm per side.

Customer Service

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